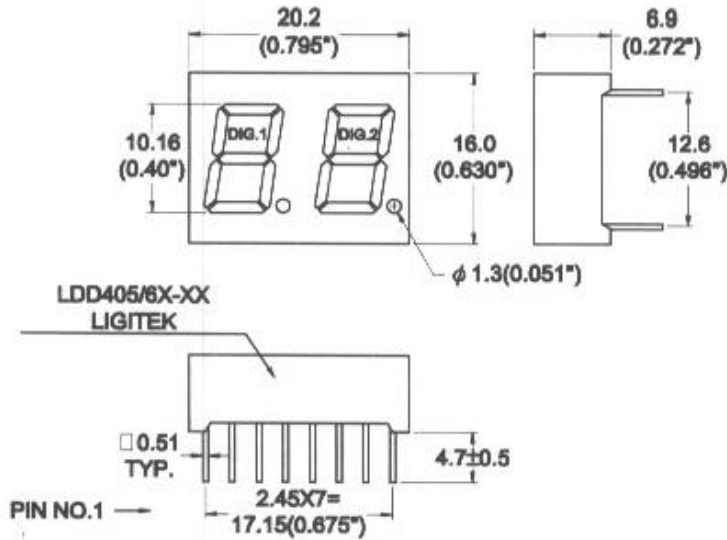
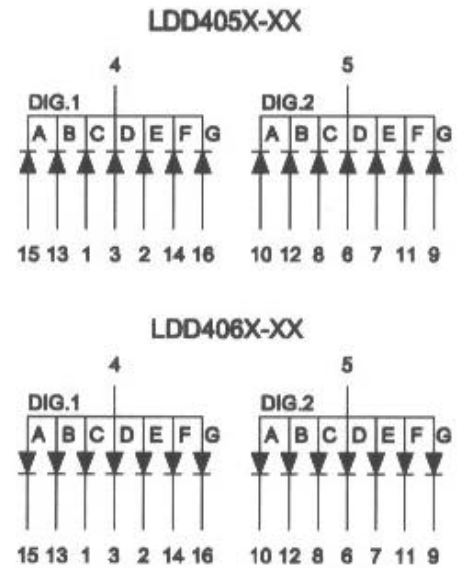


PACKAGE DIMENSION



INTERNAL CIRCUIT DIAGRAM



NOTE: 1. All Dimension Are in Millimeters And (Inch)
 Tolerance is $\pm 0.25(0.01)$ unless Otherwise Noted
 2. Specifications are subject to change without notice.

• Connection To Electrical Schematic

Electrical connection

PIN NO.	LDD405X-XX	PIN NO.	LDD406X-XX
1	Anode C Dig.1	1	Cathode C Dig.1
2	Anode E Dig.1	2	Cathode E Dig.1
3	Anode D Dig.1	3	Cathode D Dig.1
4	Common Cathode Dig.1	4	Common Anode Dig.1
5	Common Cathode Dig.2	5	Common Anode Dig.2
6	Anode D Dig.2	6	Cathode D Dig.2
7	Anode E Dig.2	7	Cathode E Dig.2
8	Anode C Dig.2	8	Cathode C Dig.2
9	Anode G Dig.2	9	Cathode G Dig.2
10	Anode A Dig.2	10	Cathode A Dig.2
11	Anode F Dig.2	11	Cathode F Dig.2
12	Anode B Dig.2	12	Cathode B Dig.2
13	Anode B Dig.1	13	Cathode B Dig.1
14	Anode F Dig.1	14	Cathode F Dig.1
15	Anode A Dig.1	15	Cathode A Dig.1
16	Anode G Dig.1	16	Cathode G Dig.1

• Part Selection And Application Information(Ratings At 25°C Ambient)

PART NO	CHIP		common cathode or anode	λ_p (nm)	$\Delta\lambda$ (nm)	Electrial					IV-M
	material	emitted				Vf(v)			Iv(mcd)		
						Min	Typ	Max	Min	Typ	
LDD4055-XX	GaAlAs	Red	Common Cathode	660	20	1.5	1.7	2.4	3.05	5.0	2:1
LDD4051-XX	GaP	Red		697	90	1.7	2.1	2.8	0.2	0.35	2:1
LDD4052-XX	GaP	Green		565	30	1.7	2.1	2.8	1.75	3.05	2:1
LDD4053-XX	GaAsP/GaP	Yellow		585	35	1.7	2.0	2.8	1.75	3.05	2:1
LDD4054-XX	GaAsP/GaP	Orange		635	45	1.7	2.0	2.8	1.75	3.05	2:1
LDD4052V-XX	GaP	Green		565	30	1.7	2.1	2.8	2.35	4.0	2:1
LDD4065-XX	GaAlAs	Red	Common Anode	660	20	1.5	1.7	2.4	3.05	5.0	2:1
LDD4061-XX	GaP	Red		697	90	1.7	2.1	2.8	0.2	0.35	2:1
LDD4062-XX	GaP	Green		565	30	1.7	2.1	2.8	1.75	3.05	2:1
LDD4063-XX	GaAsP/GaP	Yellow		585	35	1.7	2.0	2.8	1.75	3.05	2:1
LDD4064-XX	GaAsP/GaP	Orange		635	45	1.7	2.0	2.8	1.75	3.05	2:1
LDD4062V-XX	GaP	Green		565	30	1.7	2.1	2.8	2.35	4.0	2:1

• Absoult Maximum Rating (Ta=25°C)

Parameter	Red		Green		Yellow		Orange		Unit	Remark
	SR	H	VG	G	Y		E			
Forward Current Per Chip	40	15	30	30	20		30		mA	
Peak Current Per Chip (Duty 1/10,0.1mS Pulse Width)	200	60	120	120	80		120		mA	
Power Dissipation Per Chip	110	45	100		85		100		mW	
Derating Linear From 25°C Per Chip	0.45	0.25	0.45		0.45		0.45		mA/°C	
Reverse Current Per Any Chip	10		10		10		10		μA	
Operating Temperature	-25°C TO +85°C									
Storage Temperature	-25°C TO +85°C									

Solder Temperature 1-16 Inch Below Seating Plane For 3 Seconds At 260°C

• Test Condition For Each Parameter

Parameter	Symbol	Unit	Test Condition
Forward Voltage Per Chip	Vf	volt	If=20mA
Luminous Intensity Per Chip	Iv	mcd	If=10mA
Peak Emission Wavelength	λ_p	nm	If=20mA
Spectral Line Half-Width	$\Delta\lambda$	nm	If=20mA
Reverse Current Any Chip	Ir	μA	Vr=5V
Luminous Intensity Matching Ratio	IV-M		